

**N-Ch 60V Fast Switching MOSFETs**
**General Description**

The UB6006 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent R<sub>DS(ON)</sub> and gate charge for most of the synchronous buck converter applications.

The UB6006 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

**Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	45	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	28	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	7.4	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	100	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	67	mJ
I <sub>AS</sub>	Avalanche Current	28	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	74	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	2	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

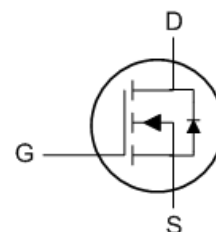
Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	1.68	°C/W

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	ID
60V	18mΩ	45A

**Applications**

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- LCD/LED back light

**TO263 Pin Configuration**


**N-Ch 60V Fast Switching MOSFETs**
**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	$BV_{DSS}$ Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.057	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=30A$	---	14	18	m $\Omega$
		$V_{GS}=4.5V, I_D=15A$	---	16	20	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.68	---	mV/ $^\circ\text{C}$
$I_{DSS}$	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	$\mu\text{A}$
		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
$I_{GSS}$	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
gfs	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	35.2	---	S
$R_g$	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.7	3.4	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{DS}=48V, V_{GS}=4.5V, I_D=15A$	---	19.3	27	nC
$Q_{gs}$	Gate-Source Charge		---	7.1	10	
$Q_{gd}$	Gate-Drain Charge		---	7.6	10.6	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=3.3\Omega, I_D=15A$	---	7.2	14.4	ns
$T_r$	Rise Time		---	50	90	
$T_{d(off)}$	Turn-Off Delay Time		---	36.4	73	
$T_f$	Fall Time		---	7.6	15.2	
$C_{iss}$	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	2423	3392	$\mu\text{F}$
$C_{oss}$	Output Capacitance		---	145	203	
$C_{riss}$	Reverse Transfer Capacitance		---	97	136	

**Guaranteed Avalanche Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
EAS	Single Pulse Avalanche Energy <sup>5</sup>	$V_{DD}=25V, L=0.1\text{mH}, I_{AS}=15A$	19	---	---	mJ

**Diode Characteristics**

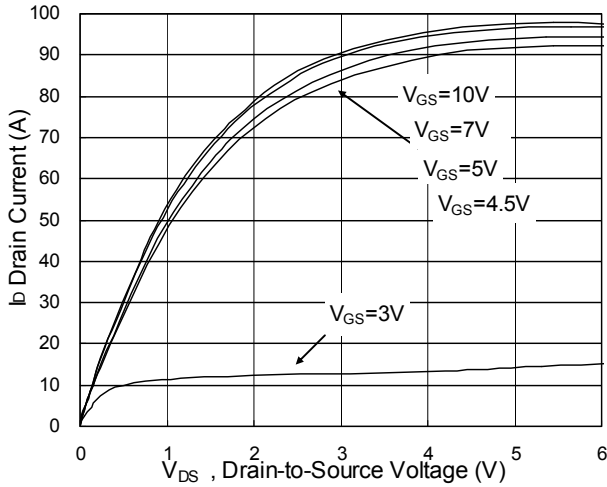
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,6</sup>	$V_G=V_D=0V$ , Force Current	---	---	45	A
$I_{SM}$	Pulsed Source Current <sup>2,6</sup>		---	---	100	A
$V_{SD}$	Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=A, T_J=25^\circ\text{C}$	---	---	1	V
$t_{rr}$	Reverse Recovery Time	$I_F=15A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	16.3	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	11	---	nC

Note :

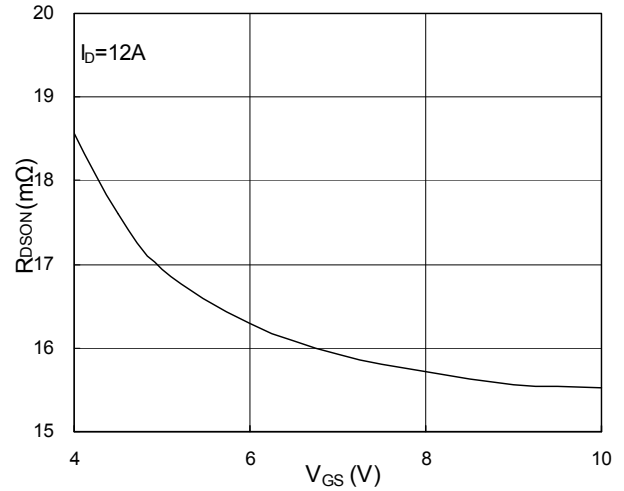
- The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- The data tested by pulsed, pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$
- The EAS data shows Max. rating. The test condition is  $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=28A$
- The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- The Min. value is 100% EAS tested guarantee.
- The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.

**N-Ch 60V Fast Switching MOSFETs**

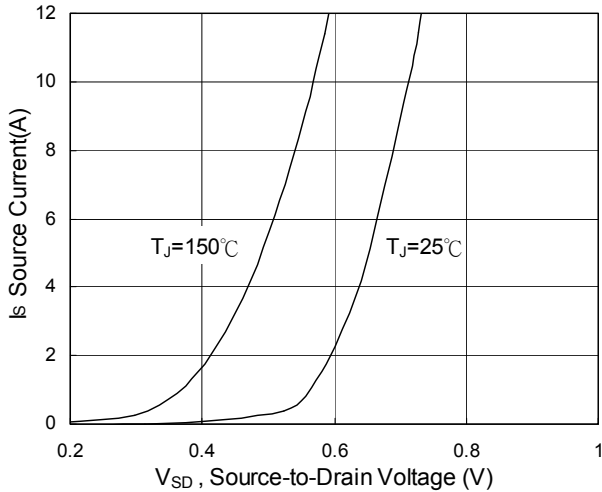
**Typical Characteristics**



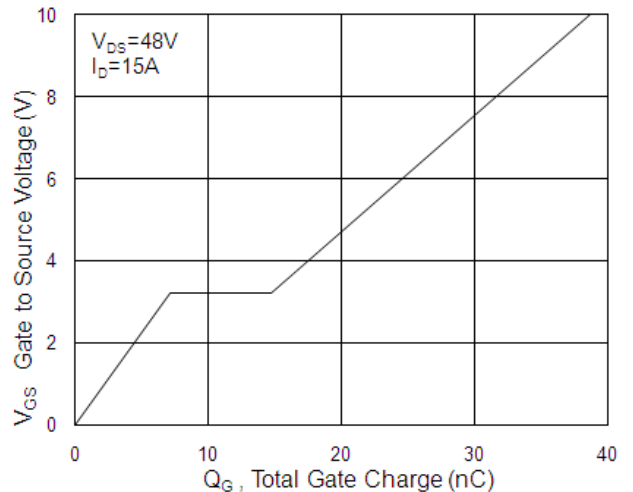
**Fig.1 Typical Output Characteristics**



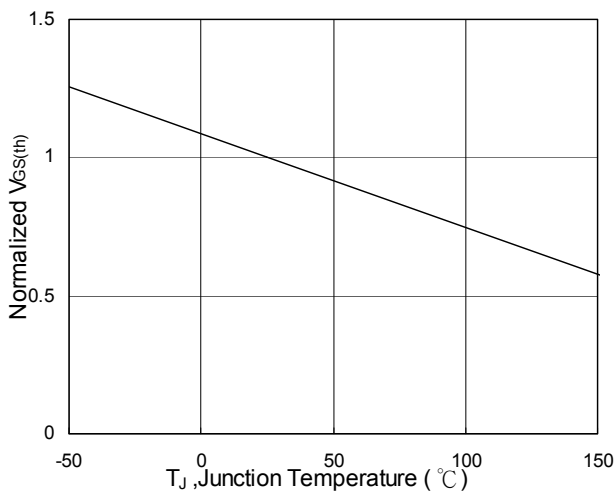
**Fig.2 On-Resistance v.s Gate-Source**



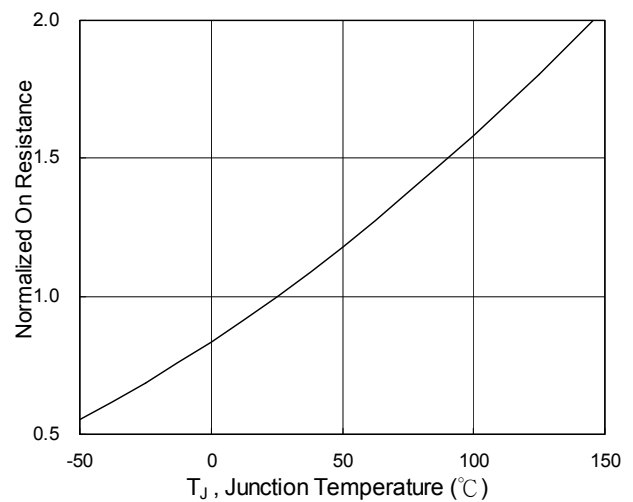
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**

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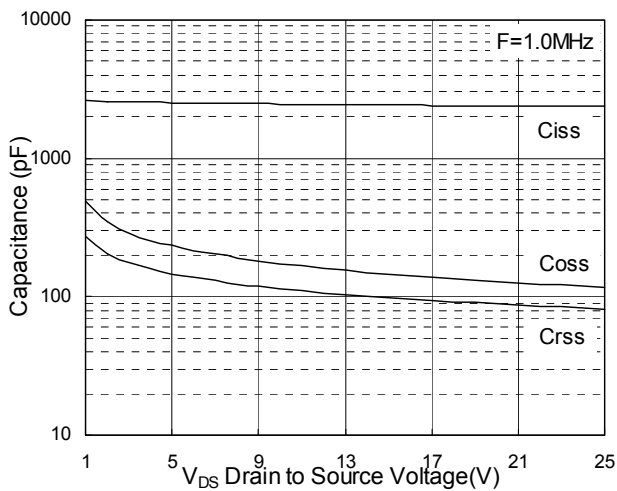


Fig.7 Capacitance

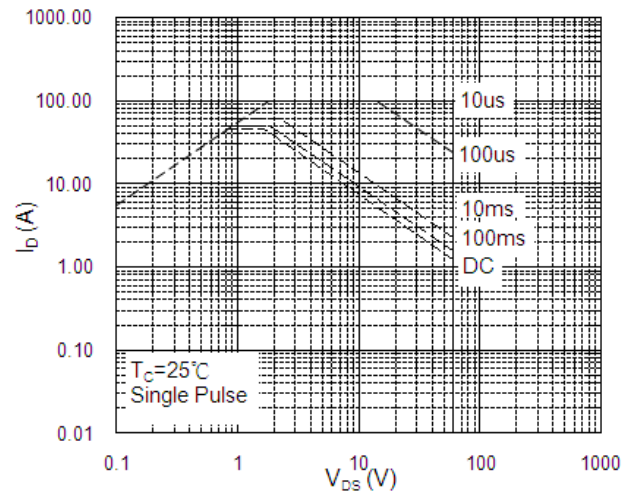


Fig.8 Safe Operating Area

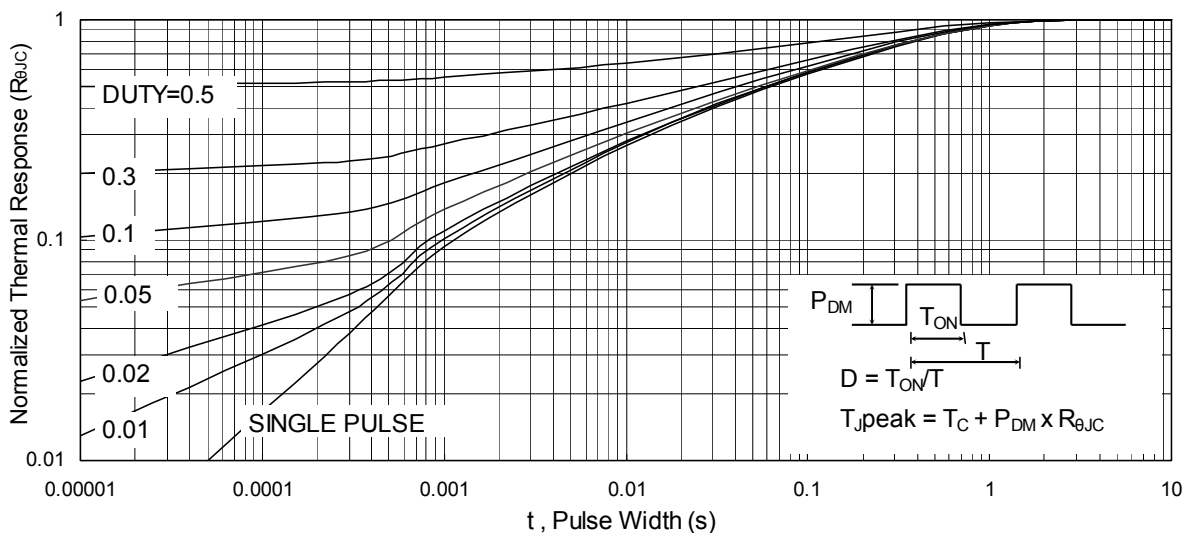


Fig.9 Normalized Maximum Transient Thermal Impedance

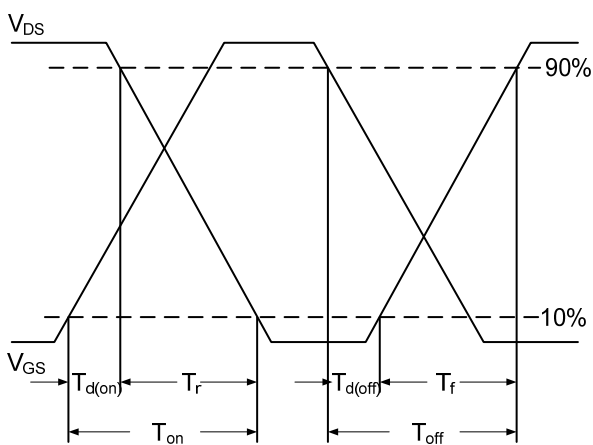


Fig.10 Switching Time Waveform

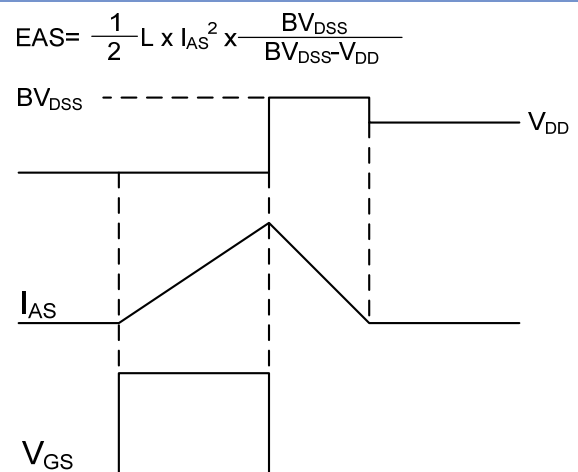


Fig.11 Unclamped Inductive Switching Waveform